

ABSTRACT OF THE DISCLOSURE

A semiconductor device including: a first gate insulating film which is pattern-formed on an N type well region within
5 a P type semiconductor substrate; a second gate insulating film which is formed on the semiconductor substrate except for this first gate insulating film; a gate electrode, which is formed in such a manner that this gate electrode is bridged over the first gate insulating film and the second gate
10 insulating film; a P type body region which is formed in such a manner that this P type body region is located adjacent to the gate electrode; an N type source region and a channel region, which are formed within this P type body region; and
15 an N type drain region which is formed at a position separated from the P type body region.